

Description

The 28N50 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

 $V_{DS} = 500V, I_{D} = 28A$

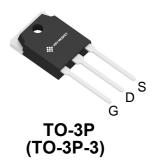
 $R_{DS(ON)} < 180 m \Omega$ @ $V_{GS}=10V$

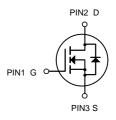
Application

High efficiency switch mode power supplies

Power factor correction

Electronic lamp ballast





N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Units Tube
28N50	TO-3P(TO-3P-3)	HXY 28N50 YYYY	50

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	500	V
VGS	Gate-Source Voltage	<u>+</u> 20	V
I _D @T _C =25°C	Drain Current	28	Α
IDM	Pulsed Drain Current ¹	112	Α
P _D @T _C =25°C	Total Power Dissipation	312.5	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·		•			
Drain-Source Breakdown Voltage (Note 1)	BV _{DSS}	V _{GS} =0V I _D =250μA	500	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =500V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	-	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =14A	-	150	180	mΩ
Forward Transconductance	g _{FS}	V _{DS} =40V,I _D =14A	-	25	-	S
Dynamic Characteristics			•			
Input Capacitance	C _{lss}	V _{DS} =25V,V _{GS} =0V,	-	4500	-	PF
Output Capacitance	Coss		-	320	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	_	20	-	PF
Switching Characteristics			•			
Turn-on Delay Time	t _{d(on)}		-	40	-	nS
Turn-on Rise Time	t _r	V_{DD} =400 V , I_{D} =28 A	-	70	-	nS
Turn-Off Delay Time	t _{d(off)}	R_G =10 $\Omega^{(Note 2)}$	-	170	-	nS
Turn-Off Fall Time	t _f		-	55	-	nS
Total Gate Charge	Qg	V _{DS} =400V,I _D =28A, V _{GS} =10V ^(Note 2)	-	110	-	nC
Gate-Source Charge	Q _{gs}		_	15	-	nC
Gate-Drain Charge	Q _{gd}	v GS-10 v	-	40	-	nC
Drain-Source Diode Characteristics				·		
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =14A	-		1.4	V
Diode Forward Current (Note 2)	Is		-	-	28	Α

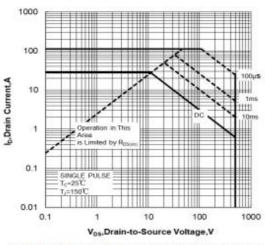
Notes:

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature.

^{2.} Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.



Typical Electrical



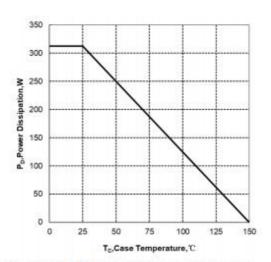
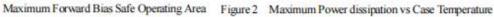
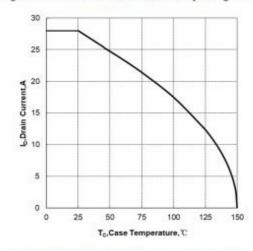


Figure 1





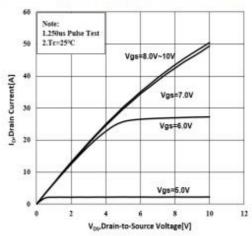


Figure 3 Maximum Continuous Drain Current vs Case Temperature

Figure 4 Typical Output Characteristics

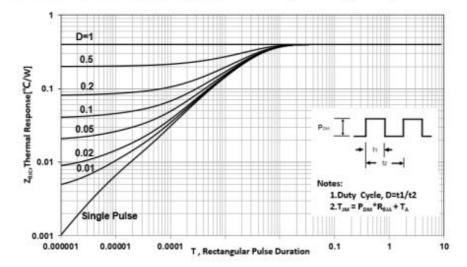


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

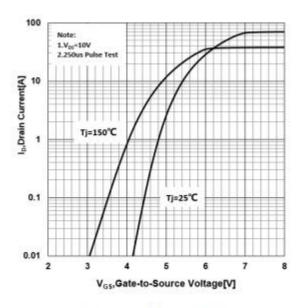


Figure 6 Typical Transfer Characteristics

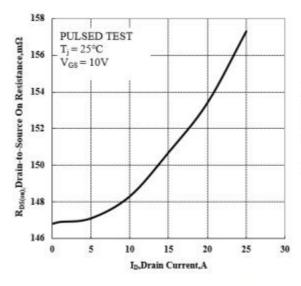


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

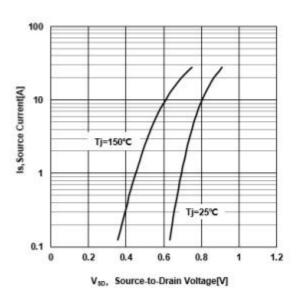


Figure 7 Typical Body Diode Transfer Characteristics

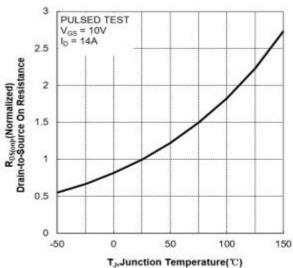


Figure 9 Typical Drian to Source on Resistance vs Junction Temperature

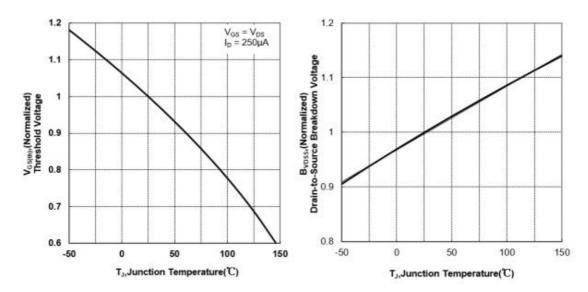


Figure 10 Typical Theshold Voltage vs Junction Temperature

Figure 11 Typical Breakdown Voltage vs Junction Temperature

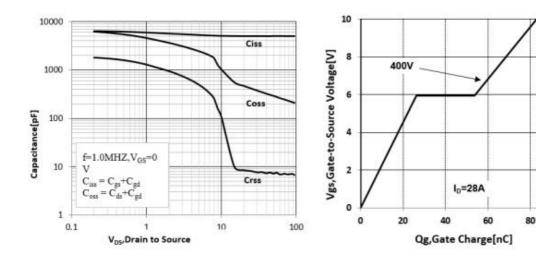


Figure 12 Typical Capacitance vs Drain to Source Voltage

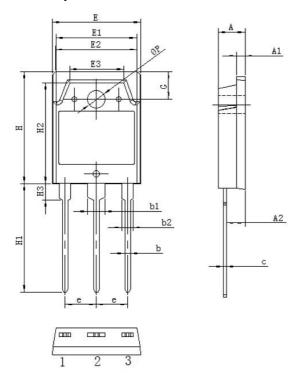
Figure 13 Typical Gate Charge vs Gate to Source Voltage

100



Package Information

TO-3P (TO-3P-3)



Symbol	单位 mm		
	Min	Nom	Max
A	4.60	4. 80	5. 00
A1	1. 3	1.5	1. 7
A2	1. 20	1.40	1. 60
b	0.80	1.0	1. 20
b1	2. 90	3. 10	3. 30
b2	1. 90	2. 10	2. 30
С	0. 50	0.60	0.70
e	5. 25	5. 45	5. 65
E	15. 2	15. 6	16. 0
E1	13. 2	13. 4	13. 6
E2	13. 1	13. 3	13. 5
E3	9. 1	9. 3	9. 5
Н	19.8	20.0	20. 2
H1	20. 1	20.3	20. 5
H2	18. 5	18. 7	18. 9
НЗ	3. 2	3. 5	3.8
G	4.8	5. 0	5. 2
ФР	3. 00	3. 20	3. 40



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